

#### **Feature**

- Precision MEMS process
- High performance, shielded, Micro-cavity structure
- Silicon substrate, 50Ω CPW output
- Au wire bonding, for MCM applications

# **Environmental Specifications**

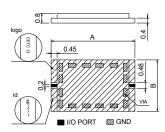
Operating Temperature	-55℃~+85℃	
Storage Temperature	-55°C∼+125°C	
Max. Input Power	35dBm	

# Electrical Specifications(T<sub>A</sub>=+25°C)

Parameter	Min.	Тур.	Max.	Unit
Center Freq. (f₀)	-	6.85	-	GHz
Pass Band	6.6	-	7.1	GHz
Ripple in Pass band	-	-	1	dB
Insertion Loss @ f₀	-	-	3	dB
Return Loss	15	-	-	dB
	≥30@6.1GHz&7.6GHz			dB
Out of band	≥40@60	dB		
Attenuation	≥60@DC~5GHz ≥60@B~11GHz ≤0.5@6.6~7.1GHz ≤±3.5@6.6~7.1GHz			dB
				dB
Group Delay Variation				ns
Linear Phase				0

S2P file name: SiMF6R85\_R5-8D3.s2p

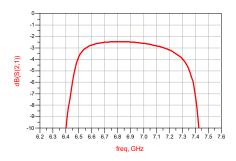
# **Outline Drawing**



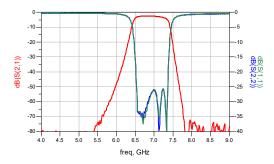
Symbol	Value (mm)		
	Min.	Nominal	Max.
А	6.9	-	7.0
В	4.8	-	4.9

## **Typical Test Curves**

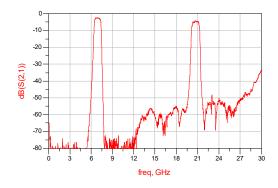
Insertion Loss VS Frequency (T<sub>A</sub>=25°C)



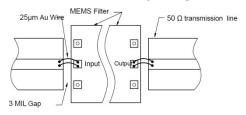
Insertion Loss & Return Loss VS Frequency (T<sub>A</sub>=25°C)



Broadband Insertion Loss VS Frequency (T<sub>A</sub>=25°C)

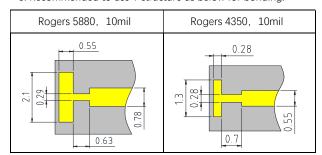


#### **Recommended Assembly Diagrams**



### **Application Notes:**

- 1. The chip is back-metalized and can be die mounted with AuSn eutectic performs or with electrically conductive epoxy (for example ME8456).
- 2. The die should be assembled on carriers like Kovar or Mu-Cu which have same Coefficient of thermal expansion. (2.9ppm/°C) with Silicon, thickness 0.2mm max.
- 3. Handle the chips in a clean environment. DO NOT attempt to clean the chip using liquid cleaning systems.
- 4. Handle the chip along the edges with a vacuum collet or with a sharp pair of bent tweezers.
- 5. Recommended to use T structure as below for bonding.



6. If you have any questions, please contact us.